



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS} (ON) Max	I _D T _C = +25°C	
40V	1.2mΩ @ V _{GS} = 10V	225A	

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low RDS(ON) Minimizes On State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

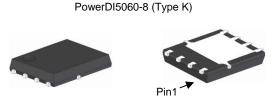
Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Engine management systems
- · Body control electronics
- DC-DC converters

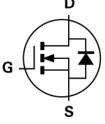
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

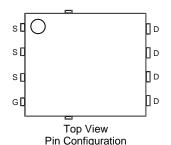




Bottom View



Internal Schematic



Ordering Information (Note 4)

		Pac	Packing			
Part Number	Package	Qty.	Carrier			
DMTH41M2SPS-13	PowerDI5060-8 (Type K)	2,500	Tape & Reel			

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ ☐ Hanufacturer's Marking
TH41M2SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 22 = 2022)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	40	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	lo	225 160	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	900	Α
Continuous Body Diode Forward Current (Note 6)	Tc = +25°C	Is	200	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Ism	900	Α	
Avalanche Current, L = 0.1mH		las	73	Α
Avalanche Energy, L = 0.1mH		E _{AS}	266	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	44	°C/W	
Total Power Dissipation (Note 6)	Tc = +25°C	PD	158	W
Thermal Resistance, Junction to Case (Note 6)	R _θ JC	0.9	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

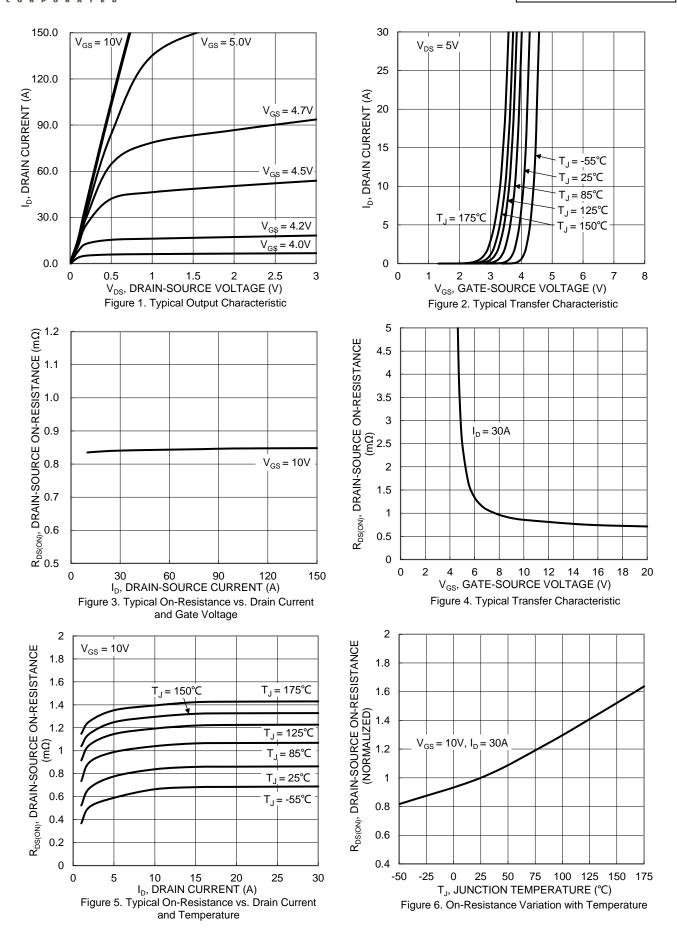
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	40		_	V	$V_{GS} = 0V$, $I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS	l	_	1	μΑ	$V_{DS} = 32V$, $V_{GS} = 0V$
Gate-Source Leakage	Igss	1	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	RDS(ON)		0.9	1.2	mΩ	$V_{GS} = 10V, I_{D} = 30A$
Diode Forward Voltage	V_{SD}		0.76	1.3	V	$V_{GS} = 0V, I_{S} = 20A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	-	11085	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	l	2793	_	pF	
Reverse Transfer Capacitance	Crss		163	_		
Gate Resistance	Rg	_	3.64	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg		138	_		V _{DD} = 20V, I _D = 50A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	_	53	_	nC	
Gate-Drain Charge	Qgd	_	10	_		
Turn-On Delay Time	tD(ON)	_	14	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{g} = 2.5\Omega$
Turn-On Rise Time	t _R	_	19	_		
Turn-Off Delay Time	tD(OFF)		90	_	ns	
Turn-Off Fall Time	tF	1	36	_		
Reverse Recovery Time	trr		60	_	ns	In - 15 A di/dt - 100 A /u.o
Reverse Recovery Charge	QrR		90	_	nC	I _F = 15A, di/dt = 100A/μs

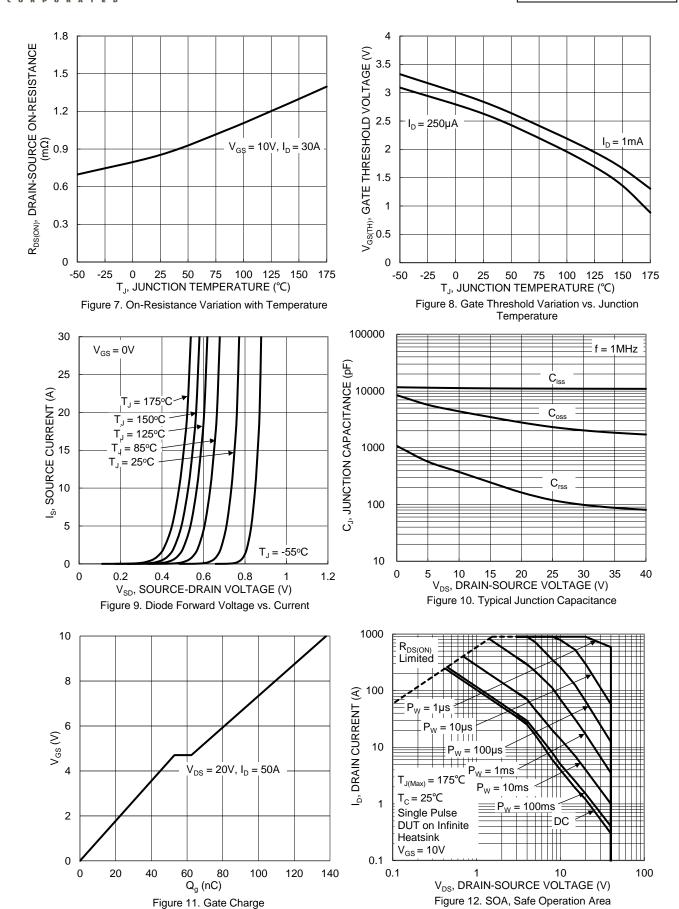
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.











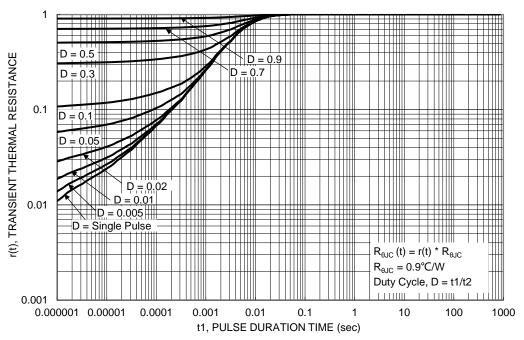


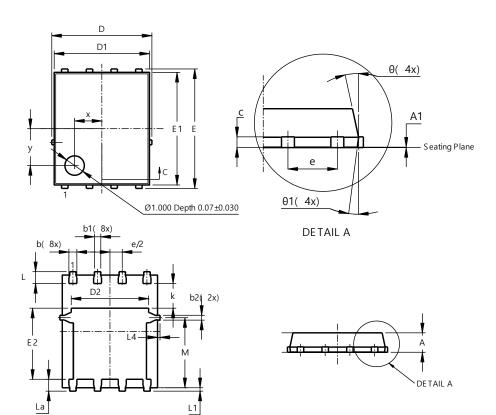
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

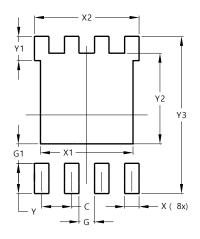


PowerDI5060-8 (Type K)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05	0.02	
b	0.33	0.51	0.41	
b1	0.300	0.366	0.333	
b2	0.20	0.35	0.25	
C D	0.23	0.33	0.277	
	5	.15 BS0		
D1	4.85	4.95	4.90	
D2	-	-	3.98	
Е	6	.15 BS0	\sim	
E1	5.75	5.85	5.80	
E2	3.56	3.725	3.66	
е	1	.27BSC		
k	-	-	1.27	
L	0.51	0.71	0.61	
La	0.51	0.675	0.61	
L1	0.05	0.20	0.175	
L4	-	-	0.125	
М	3.50	3.71	3.605	
Х	-	-	1.400	
у	-	-	1.900	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value		
Difficitsions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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